

COMPLIANCE

TSM35N03PQ56 30V N-Channel Power MOSFET

R_{DS(on)}(mΩ)

7 @ V_{GS}=10V

9 @ V_{GS}=4.5V

I_D (A)

12

10

PRODUCT SUMMARY

V_{DS} (V)

30

PDFN 5x6

Pin Definition:1. Source8. Drain2. Source7. Drain	
1. Source	8. Drain
2. Source	7. Drain
3. Source	6. Drain
4. Gate	5. Drain

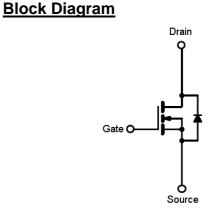
Features

- Advanced Trench Technology
- Low On-Resistance
- Low gate charge typical @ 8.2nC (Typ.)
- Low Crss typical @ 90pF (Typ.)

Ordering Information

Part No.	Package	Packing
TSM35N03PQ56 RLG	PDFN56	2.5Kpcs / 13" Reel

Note: "G" denote for Halogen Free Product



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V _{GS}	±25	V	
Continuous Drain Current	T _C =25℃		35		
	T _C =70℃		35	А	
	T _A =25℃	- I _D	22		
	T _A =70℃		18		
Drain Current-Pulsed Note 1		I _{DM}	60	А	
Avalanche Current, L=0.5mH		I _{AS} , I _{AR}	26	А	
Avalanche Energy, L=0.5mH		E_{AS},E_{AR}	33	mJ	
Maximum Power Dissipation	T _C =25℃		35		
	T _C =70℃		23	W	
	T _A =25℃	P _D	4.2		
	T _A =70℃		2.7		
Storage Temperature Range		T _{STG}	-55 to +150	ĉ	
Operating Junction Temperature Range		TJ	-55 to +150	ĉ	

* Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R⊖ _{JC}	3.5	°C/W
Thermal Resistance - Junction to Ambient	RƏ _{JA}	30	°C/W

Notes: Surface mounted on FR4 board t \leq 10sec



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Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static		_			1	
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250uA$	BV _{DSS}	30			V
Drein Course On State Desistance	$V_{GS} = 10V, I_{D} = 12A$	R _{DS(ON)}		5.5	7	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 10A$			7.5	9	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 uA$	V _{GS(TH)}	1.3		2.5	V
Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$	I _{DSS}			1	uA
Gate Body Leakage	$V_{GS} = \pm 25V, V_{DS} = 0V$	I _{GSS}			±100	nA
Dynamic						
Total Gate Charge		Qg		8.2		nC
Gate-Source Charge	$V_{DS} = 15V, I_D = 16A,$ $V_{GS} = 4.5V$	Q _{gs}		2.7		
Gate-Drain Charge		Q _{gd}		2.2		
Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V,$	C _{iss}		1050		
Output Capacitance		C _{oss}		210		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		90		
Switching						
Turn-On Delay Time		t _{d(on)}		9		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 15V,$	t _r		9		- 0
Turn-Off Delay Time	$R_G = 1\Omega$	t _{d(off)}		20		nS
Turn-Off Fall Time		t _f		7		
Drain-Source Diode Characteristic	s and Maximum Rating					
Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =2.3A	V_{SD}		0.75	1.3	V
Reverse Recovery Time	I _S = 3.2A, T _J =25 °C	t _{fr}		22		nS
Reverse Recovery Charge	dl/dt = 100A/us	Q _{fr}		14		nC

Notes:

1. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

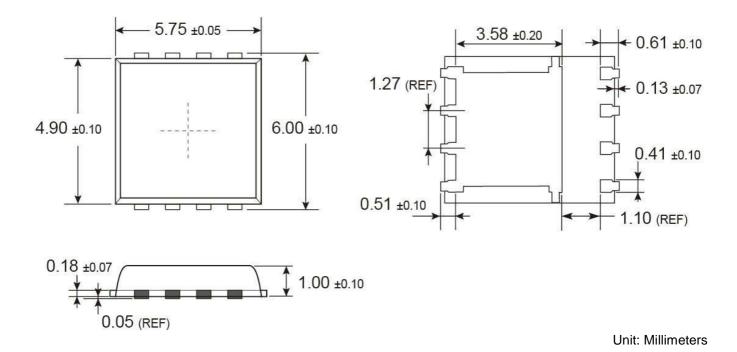
2. $R\theta_{JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R\theta_{JC}$ is guaranteed by design while $R\theta_{CA}$ is determined by the user's board design. $R\theta_{JA}$ shown below for single device operation on FR-4 in still air

3. The maximum current rating is limited by package.



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PDFN56 Mechanical Drawing





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